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# DISCRETE POWER DIODES and THYRISTORS DATA BOOK



## ST280CH..C SERIES

#### PHASE CONTROL THYRISTORS

Features

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case TO-200AB (A-PUK)
- Extended temperature range

#### **Typical Applications**

- DC motor controls
- Controlled DC power supplies
- AC controllers

#### Major Ratings and Characteristics

Parameters		ST280CHC	Units	
I <sub>T(AV)</sub>		500	A	
	@ T <sub>hs</sub>	80	°C	
I <sub>T(RMS)</sub>		1130	А	
	@ T <sub>hs</sub>	25	°C	
I <sub>TSM</sub>	@ 50Hz	7200	А	
	@ 60Hz	7500	A	
l <sup>2</sup> t	@ 50Hz	260	KA <sup>2</sup> s	
	@ 60Hz	230	KA <sup>2</sup> s	
V <sub>DRM</sub> /V <sub>RRI</sub>	м	400 to 600	V	
t <sub>q</sub>	typical	100	μs	
TJ		- 40 to 150	°C	



**Hockey Puk Version** 

500A

## ELECTRICAL SPECIFICATIONS Voltage Ratings

	<b>j</b> -			
Type number	Voltage Code	V <sub>DRM</sub> /V <sub>RRM</sub> , max. repetitive peak and off-state voltage	V <sub>RSM</sub> , maximum non- repetitive peak voltage	I <sub>DRM</sub> /I <sub>RRM</sub> max. @ T, = T, max
		V	V	mA
ST280CHC	04	400	500	75
51280CHC	06	600	700	75

#### **On-state Conduction**

	Parameter	ST280CHC	Units	Conditions	Conditions		
I <sub>T(AV)</sub>	Max. average on-state current	500 (185)	А	180° conduction, half sine wave			
	@ Heatsink temperature	80 (110)	°C	double side (single side) cooled			
I <sub>T(RMS)</sub>	Max. RMS on-state current	1130		DC @ 25°C	C heatsink temp	erature double side cooled	
I <sub>TSM</sub>	Max. peak, one-cycle	7200		t = 10ms	No voltage		
	non-repetitive surge current	7500	А	t = 8.3ms	reapplied		
		6000		t = 10ms	100% V <sub>RRM</sub>		
		6300		t = 8.3ms	reapplied	Sinusoidal half wave,	
l <sup>2</sup> t	Maximum I <sup>2</sup> t for fusing	260		t = 10ms	No voltage	Initial $T_j = T_j$ max.	
		235	KA <sup>2</sup> s	t = 8.3ms	reapplied		
		180	KA-S	t = 10ms	100% V <sub>RRM</sub>		
		165		t = 8.3ms	reapplied		
l²√t	Maximum $I^2 \sqrt{t}$ for fusing	2600	KA²√s	t = 0.1 to 10ms, no voltage reapplied			
V <sub>T(TO)1</sub>	Low level value of threshold						
. ,	voltage	0.84		$(16.7\% \text{ x } \pi \text{ x } I_{T(AV)} < I < \pi \text{ x } I_{T(AV)}), T_{J} = T_{J} \text{ max}$			
V <sub>T(TO)2</sub>	High level value of threshold	0.00	V				
( - )=	voltage	0.88		$(I > \pi \times I_{T(AV)}), T_J = T_J max.$			
r <sub>t1</sub>	Low level value of on-state	0.50					
	slope resistance	0.50		$(16.7\% \ x \ \pi \ x \ I_{T(AV)} < I < \pi \ x \ I_{T(AV)}), \ T_{J} = T_{J} \ max.$			
r <sub>t2</sub>	High level value of on-state	0.47	mΩ	$(  > \pi x $	)T - T mov	,	
	slope resistance	0.47		(1 > 11 × 1 <sub>T(A</sub>	$(V)$ , $T_J = T_J max$		
V <sub>TM</sub>	Max. on-state voltage	1.35	V	$I_{pk}$ = 1000A, $T_{J}$ = $T_{J}$ max, $t_{p}$ = 10ms sine pulse		t <sub>p</sub> = 10ms sine pulse	
I <sub>H</sub>	Maximum holding current	600				•	
IL.	Max (typical) latching current	1000 (300)	mA	$T_J = 25^{\circ}C$ , anode supply 12V resistive load			

#### Switching

	Parameter	ST280CHC	Units	Conditions
di/dt	Max. non-repetitive rate of rise of turned-on current	1000	A/µs	Gate drive 20V, 20 $\Omega$ , t <sub>r</sub> $\leq$ 1µs T <sub>J</sub> = T <sub>J</sub> max, anode voltage $\leq$ 80% V <sub>DRM</sub>
t <sub>d</sub>	Typical delay time	1.0	116	Gate current 1A, di $_g/dt = 1A/\mu s$ V <sub>d</sub> = 0.67% V <sub>DRM</sub> , T <sub>J</sub> = 25°C
t <sub>q</sub>	Typical turn-off time	100	μs	$\begin{split} I_{TM} &= 300\text{A}, \ T_J = T_J \ \text{max}, \ \text{di/dt} = 20\text{A}/\mu\text{s}, \ V_R = 50\text{V} \\ \text{dv/dt} &= 20\text{V}/\mu\text{s}, \ \text{Gate 0V } 100\Omega, \ t_p = 500\mu\text{s} \end{split}$

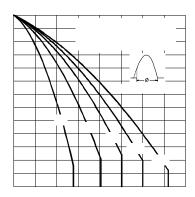


Fig. 3 - Current Ratings Characteristics

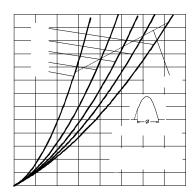


Fig. 5- On-state Power Loss Characteristics

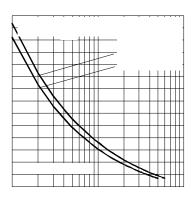


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

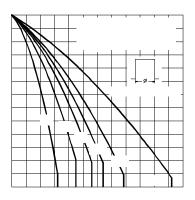


Fig. 4 - Current Ratings Characteristics

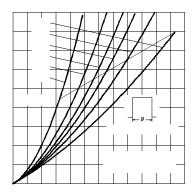


Fig. 6- On-state Power Loss Characteristics

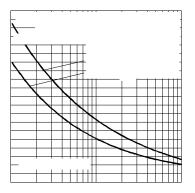


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled



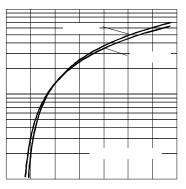


Fig. 9 - On-state Voltage Drop Characteristics

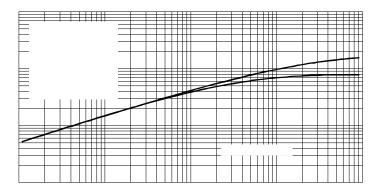


Fig. 10 - Thermal Impedance  $\rm Z_{thJ-hs}$  Characteristics

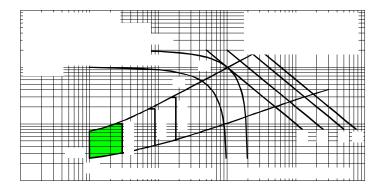


Fig. 11 - Gate Characteristics

#### Blocking

	Parameter ST280CHC		Units	Conditions
dv/dt	Maximum critical rate of rise of off-state voltage	500	V/µs	$T_J = T_J$ max. linear to 80% rated $V_{DRM}$
I <sub>DRM</sub> I <sub>RRM</sub>	Max. peak reverse and off-state leakage current	75	mA	$T_{J} = T_{J} max$ , rated $V_{DRM}/V_{RRM}$ applied

## Triggering

	Parameter	ST280CHC		Units	Conditions		
P <sub>GM</sub>	Maximum peak gate power	10.0			$T_{J} = T_{J} max, t_{p}$	<sub>p</sub> ≤ 5ms	
P <sub>G(AV)</sub>	Maximum average gate power	2.	0	W		= 50Hz, d% = 50	
I <sub>GM</sub>	Max. peak positive gate current	3.	0	А	$T_{j} = T_{j} max, t_{p} \le 5ms$		
+V <sub>GM</sub>	Maximum peak positive gate voltage	20		.,			
-V <sub>GM</sub>	Maximum peak negative gate voltage	5.	0	V	$T_J = T_J max, t_p \le 5ms$		
		TYP.	MAX.				
I <sub>GT</sub>	DC gate current required	180	-		$T_J = -40^{\circ}C$		
61	to trigger	90	150	mA	$T_J = 25^{\circ}C$	Max. required gate trigger/ cur-	
		30	-		$T_J = 150^{\circ}C$	rent/voltage are the lowest value	
		2.9	-		$T_J = -40^{\circ}C$	which will trigger all units 12V anode-to-cathode applied	
V <sub>GT</sub>	DC gate voltage required to trigger	1.8	3.0	V	$T_J = 25^{\circ}C$		
	to trigger	1.0	-		T <sub>J</sub> = 150°C		
I <sub>GD</sub>	DC gate current not to trigger	10 0.30		mA		Max. gate current/voltage not to	
V <sub>GD</sub>	DC gate voltage not to trigger			V	T <sub>J</sub> = T <sub>J</sub> max	trigger is the max. value which will not trigger any unit with rated V <sub>DRM</sub> anode-to-cathode applied	

## Thermal and Mechanical Specification

	Parameter	ST280CHC	Units	Conditions
TJ	Max. operating temperature range	-40 to 150	°C	
T <sub>stg</sub>	Max. storage temperature range	-40 to 150	C	
R <sub>thJ-h</sub>	Max. thermal resistance,	0.17		DC operation single side cooled
	junction to heatsink	0.08	K/W	DC operation double side cooled
R <sub>thC-h</sub>	s Max. thermal resistance,	0.033	K/W	DC operation single side cooled
	case to heatsink	0.017	rx/ vv	DC operation double side cooled
F	Mounting force, ± 10%	4900	N	
		(500)	(Kg)	
wt	Approximate weight	50	g	
Case style		TO - 200AB (A-PUK)		See Outline Table

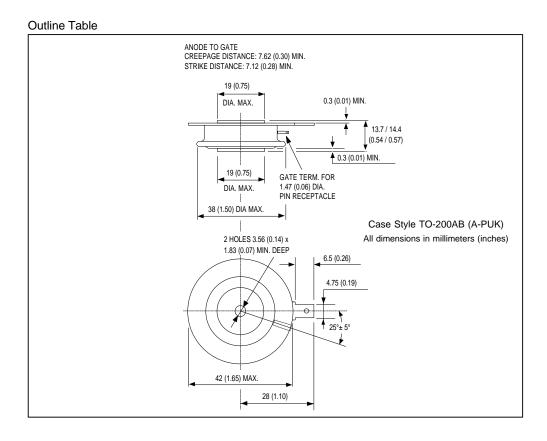
$\Delta R_{th,l-hs}$	Conduction
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 $R_{thJ-hs}$  when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal	Sinusoidal conduction		r conduction	Units	Conditions
	Single Side	Double Side	Single Side	Double Side	Units	Conditions
180°	0.016	0.017	0.011	0.011		T <sub>J</sub> = T <sub>J</sub> max.
120°	0.019	0.019	0.019	0.019		
90°	0.024	0.024	0.026	0.026	K/W	
60°	0.035	0.035	0.036	0.037		
30°	0.060	0.060	0.060	0.061		

#### Ordering Information Table

Device Code	ST 28 0 CH 06 C 1   1 2 3 4 5 6 7 8
1 - Thyristor	
2 - Essential part	t number
<b>3</b> - 0 = Converter	r grade
4 - CH = Ceramie	c Puk, High temperature
5 - Voltage code:	: Code x 100 = V <sub>RRM</sub> (See Voltage Rating Table)
6 - C = Puk Case	е ТО-200АВ (А-РИК)
7 - 0 = Eyelet ter	minals (Gate and Auxiliary Cathode Unsoldered Leads)
1 = Fast-on te	erminals (Gate and Auxiliary Cathode Unsoldered Leads)
2 = Eyelet ter	minals (Gate and Auxiliary Cathode Soldered Leads)
3 = Fast-on te	erminals (Gate and Auxiliary Cathode Soldered Leads)
8 - Critical dv/dt:	None = 500V/µsec (Standard selection)
	L = 1000V/µsec (Special selection)



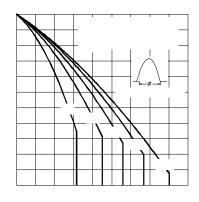


Fig. 1 - Current Ratings Characteristics

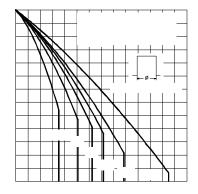


Fig. 2 - Current Ratings Characteristics